



PMZ600UNEL

20 V, N-channel Trench MOSFET

28 June 2016

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low leakage current
- Leadless ultra small SMD plastic package: $1.0 \times 0.6 \times 0.48$ mm
- ElectroStatic Discharge (ESD) protection > 1 kV HBM
- Drain-source on-state resistance $R_{DSon} = 470$ m Ω

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_J = 25$ °C		-	-	20	V
V_{GS}	gate-source voltage			-8	-	8	V
I_D	drain current	$V_{GS} = 4.5$ V; $T_{amb} = 25$ °C	[1]	-	-	0.6	A
Static characteristics							
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5$ V; $I_D = 0.6$ A; $T_J = 25$ °C		-	470	620	m Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

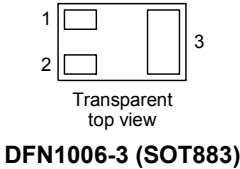
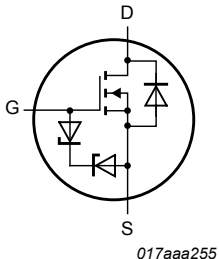


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 Transparent top view DFN1006-3 (SOT883)	 017aaa255
2	S	source		
3	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMZ600UNEL	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883

7. Marking

Table 4. Marking codes

Type number	Marking code
PMZ600UNEL	L3

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	0.6	A
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	0.4	A
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	2.5	A
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T _{sp} = 25 °C		-	2700	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	0.4	A

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

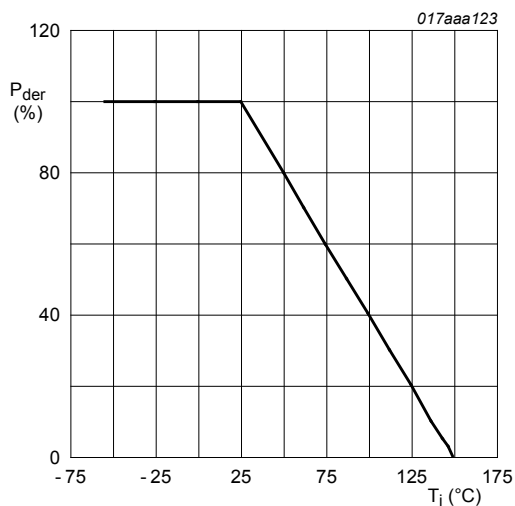


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$

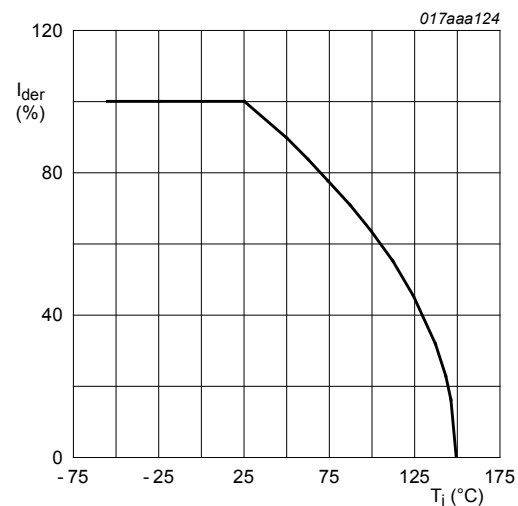
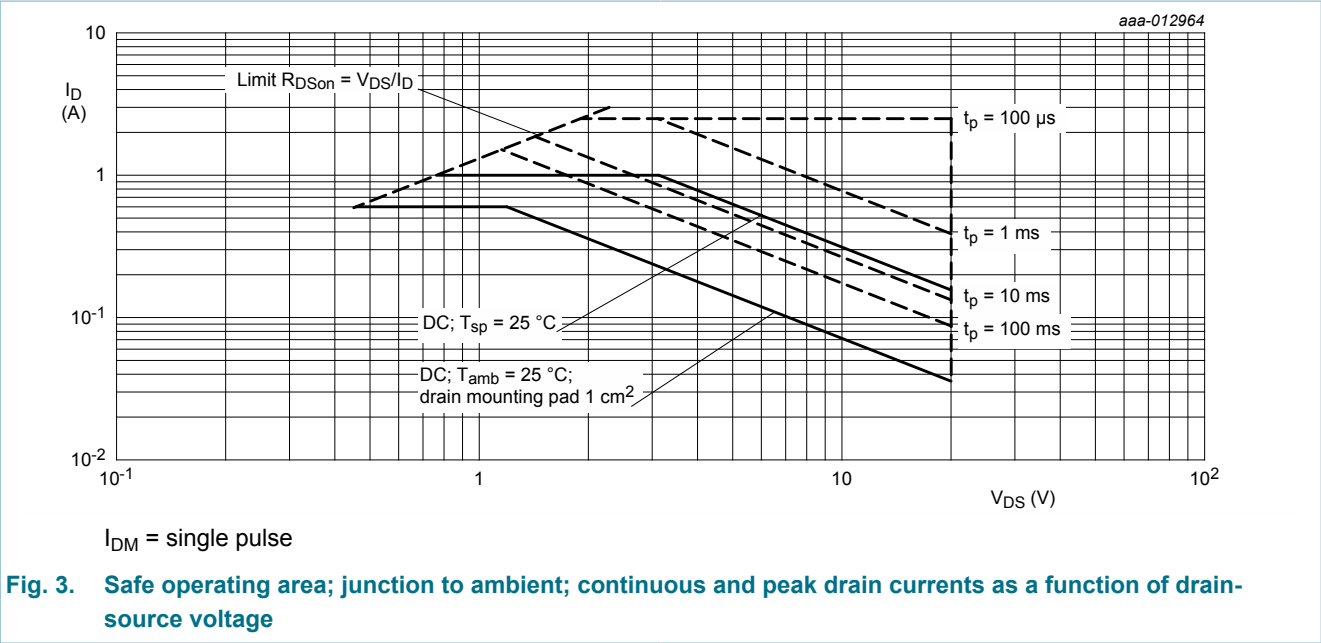


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	305	360	K/W
			[2]	-	150	175	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	40	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm^2 .

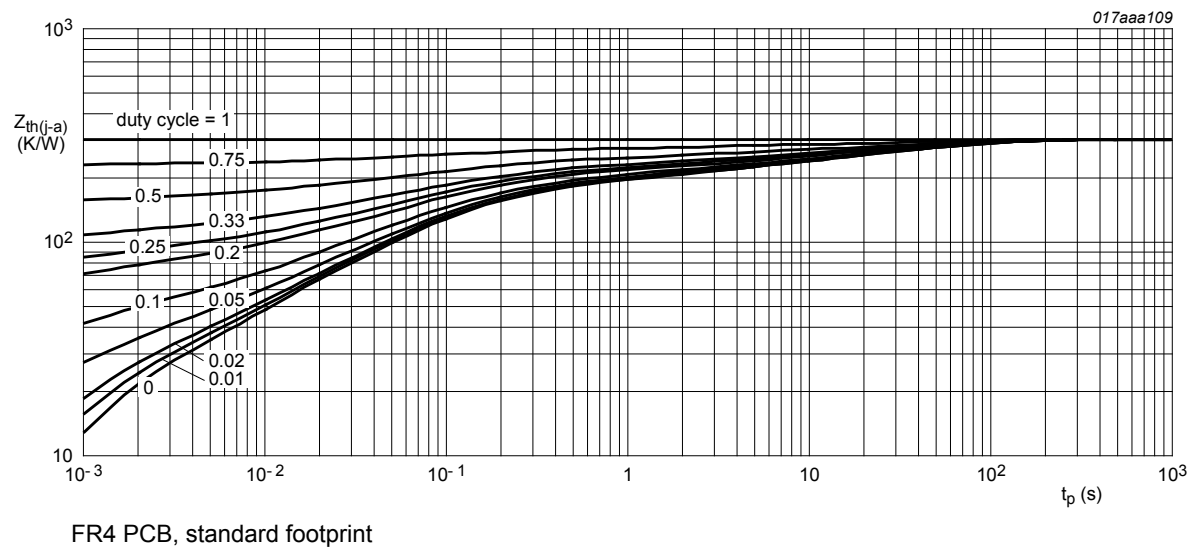


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

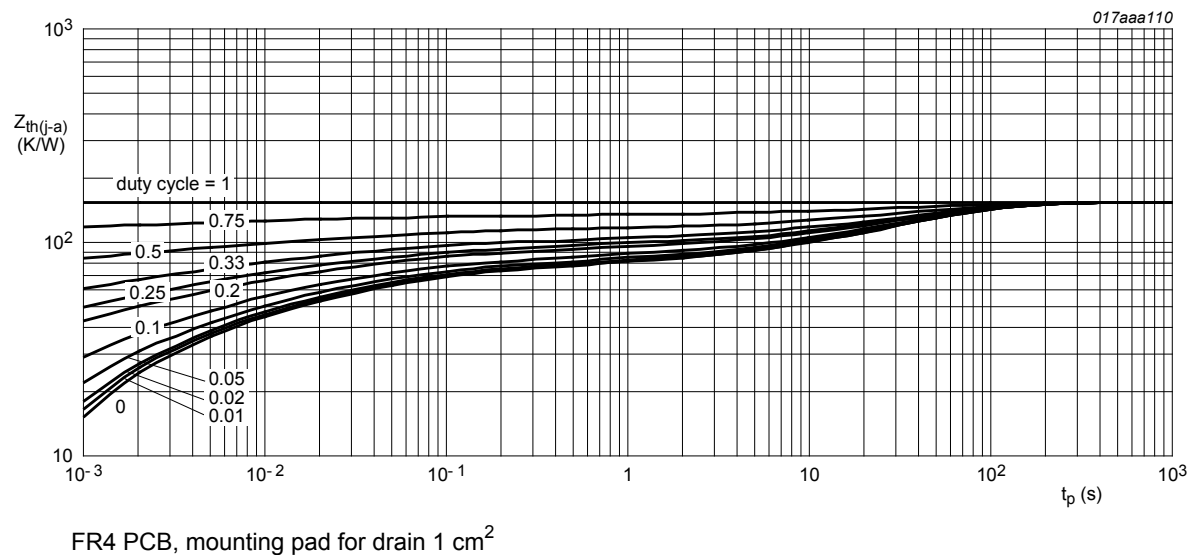


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu A$; $V_{GS} = 0\ V$; $T_j = 25\ ^\circ C$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250\ \mu A$; $V_{DS} = V_{GS}$; $T_j = 25\ ^\circ C$	0.45	0.7	0.95	V
I_{DSS}	drain leakage current	$V_{DS} = 20\ V$; $V_{GS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	1	μA
		$V_{DS} = 20\ V$; $V_{GS} = 0\ V$; $T_j = 150\ ^\circ C$	-	-	10	μA
		$V_{DS} = 5\ V$; $V_{GS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	25	nA
I_{GSS}	gate leakage current	$V_{GS} = 8\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	10	μA
		$V_{GS} = -8\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	-10	μA
		$V_{GS} = 4.5\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	1	μA
		$V_{GS} = -4.5\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	-1	μA
		$V_{GS} = 1.8\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	50	nA
		$V_{GS} = -1.8\ V$; $V_{DS} = 0\ V$; $T_j = 25\ ^\circ C$	-	-	-50	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5\ V$; $I_D = 0.6\ A$; $T_j = 25\ ^\circ C$	-	470	620	m Ω
		$V_{GS} = 4.5\ V$; $I_D = 0.6\ A$; $T_j = 150\ ^\circ C$	-	760	1000	m Ω
		$V_{GS} = 2.5\ V$; $I_D = 0.5\ A$; $T_j = 25\ ^\circ C$	-	620	850	m Ω
		$V_{GS} = 1.8\ V$; $I_D = 0.1\ A$; $T_j = 25\ ^\circ C$	-	845	1300	m Ω
		$V_{GS} = 1.5\ V$; $I_D = 10\ mA$; $T_j = 25\ ^\circ C$	-	1125	3000	m Ω
		$V_{GS} = 1.2\ V$; $I_D = 1\ mA$; $T_j = 25\ ^\circ C$	-	2210	-	m Ω
g_{fs}	forward transconductance	$V_{DS} = 5\ V$; $I_D = 0.6\ A$; $T_j = 25\ ^\circ C$	-	1	-	S
R_G	gate resistance	$f = 1\ MHz$	-	34	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 10\ V$; $I_D = 0.6\ A$; $V_{GS} = 4.5\ V$; $T_j = 25\ ^\circ C$	-	0.4	0.7	nC
Q_{GS}	gate-source charge		-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.1	-	nC
C_{iss}	input capacitance	$V_{DS} = 10\ V$; $f = 1\ MHz$; $V_{GS} = 0\ V$; $T_j = 25\ ^\circ C$	-	21.3	-	pF
C_{oss}	output capacitance		-	5.4	-	pF
C_{rss}	reverse transfer capacitance		-	4.2	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 10\ V$; $I_D = 0.6\ A$; $V_{GS} = 4.5\ V$; $R_{G(ext)} = 6\ \Omega$; $T_j = 25\ ^\circ C$	-	5.6	-	ns
t_r	rise time		-	9.2	-	ns

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
t _{d(off)}	turn-off delay time			-	19	-	ns
t _f	fall time			-	51	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 0.36 A; V _{GS} = 0 V; T _j = 25 °C		-	0.8	1.2	V

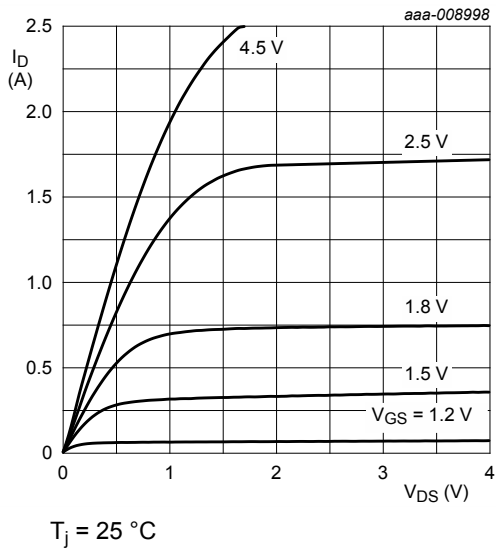


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

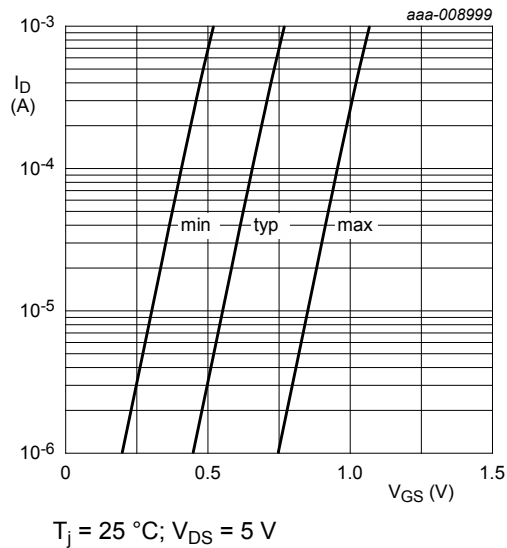


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

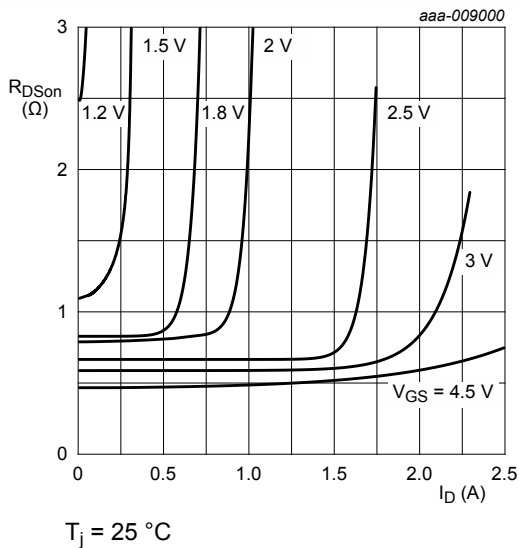


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

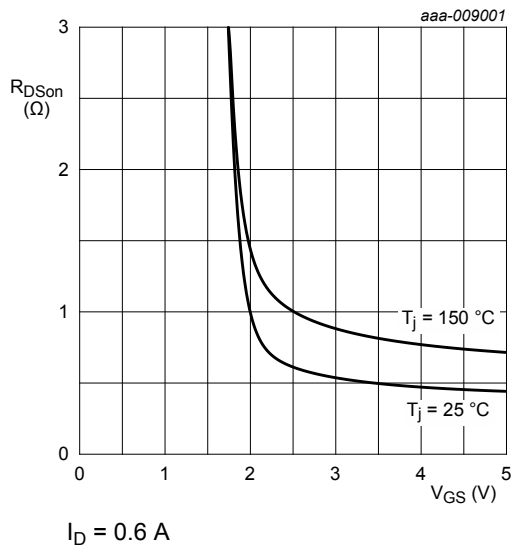


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

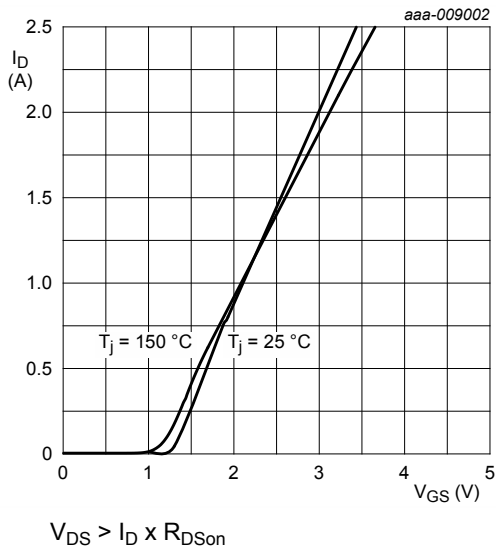


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

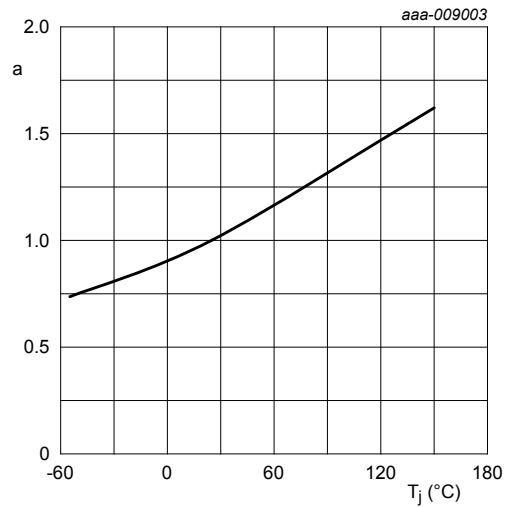


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}\text{C})}}$$

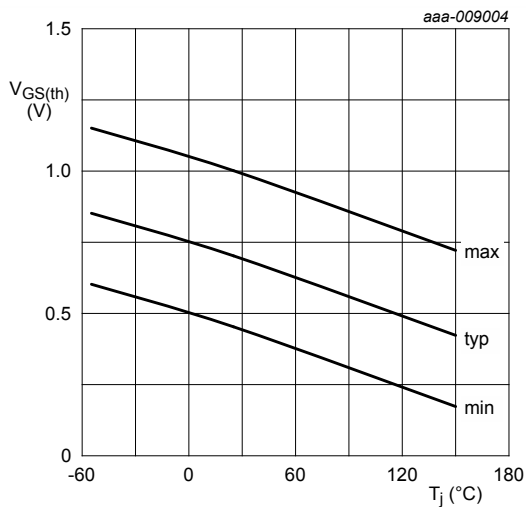


Fig. 12. Gate-source threshold voltage as a function of junction temperature

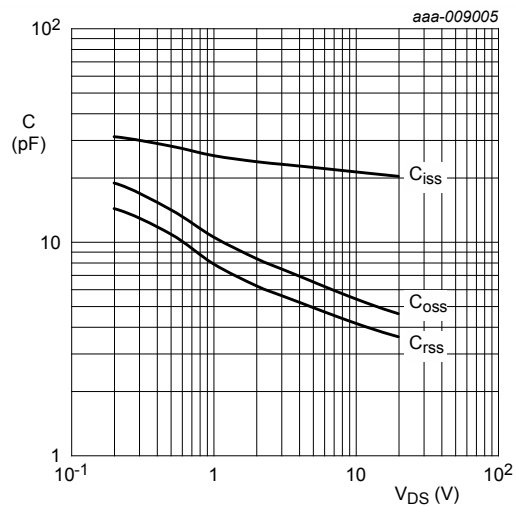


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

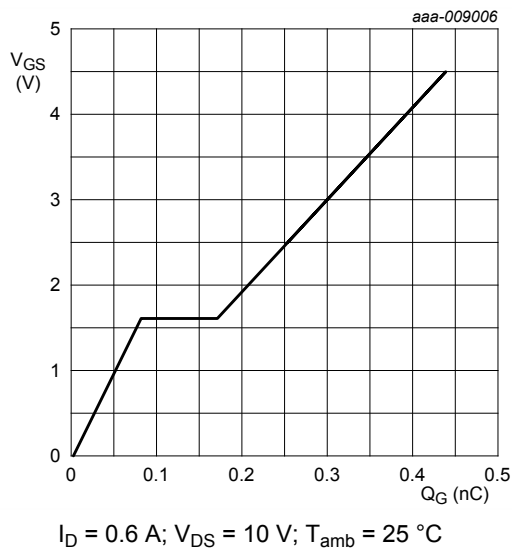


Fig. 14. Gate-source voltage as a function of gate charge; typical values

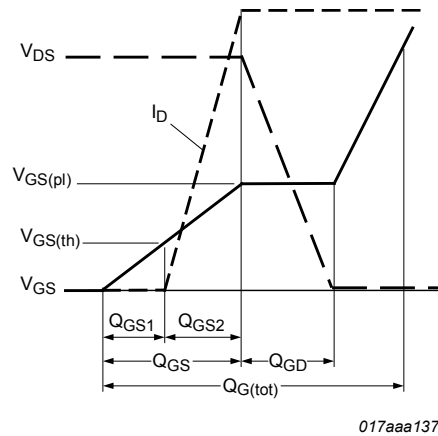


Fig. 15. MOSFET transistor: Gate charge waveform definitions

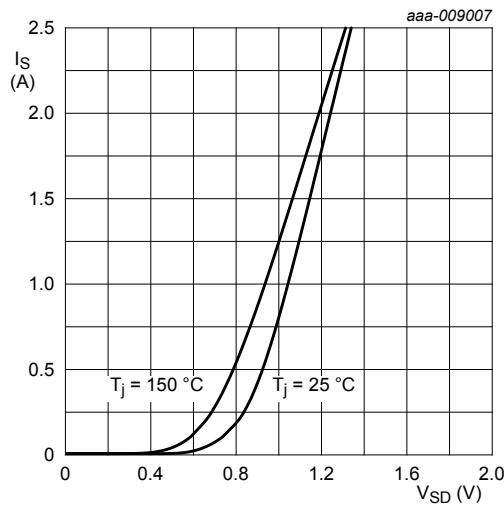


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

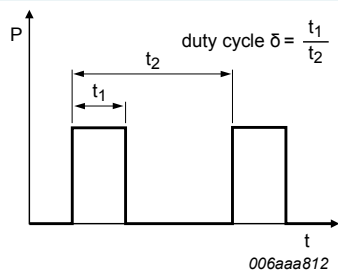


Fig. 17. Duty cycle definition

12. Package outline

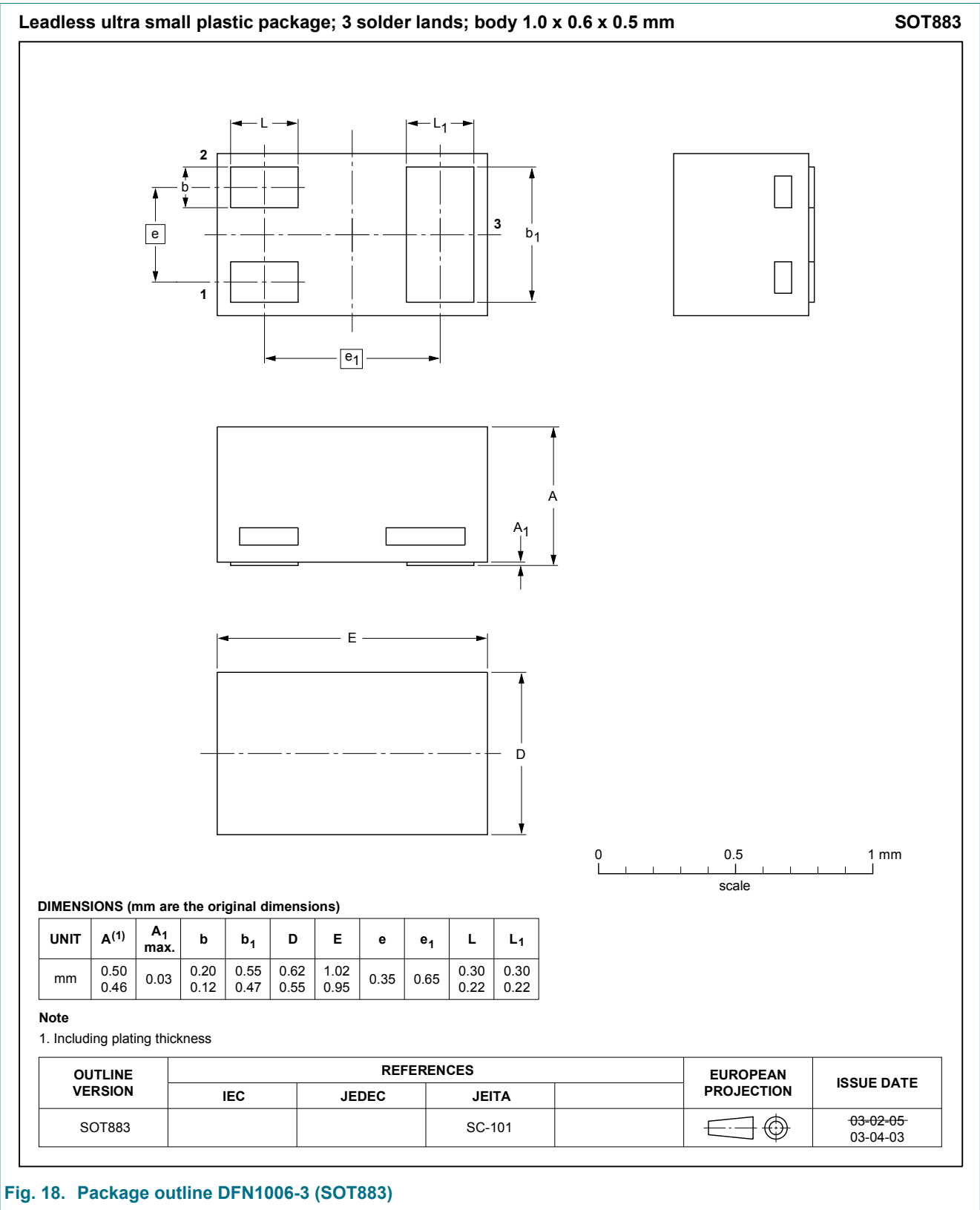


Fig. 18. Package outline DFN1006-3 (SOT883)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZ600UNEL v.1	20160628	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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